

# *Explorations in Cryogenic High-Q Mechanical Resonators*

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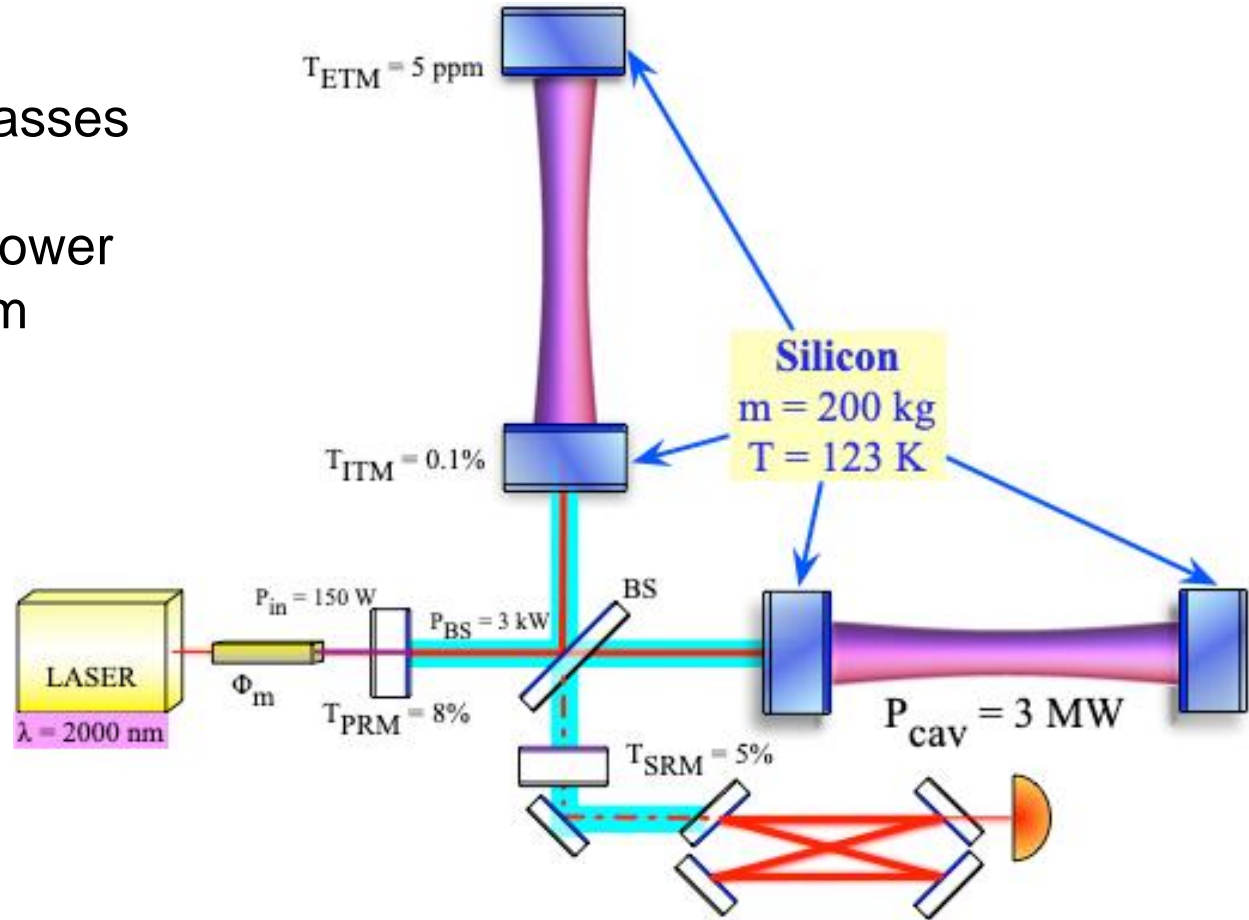
Mentors : Aaron Markowitz, Duo Tao, Rana Adhikari

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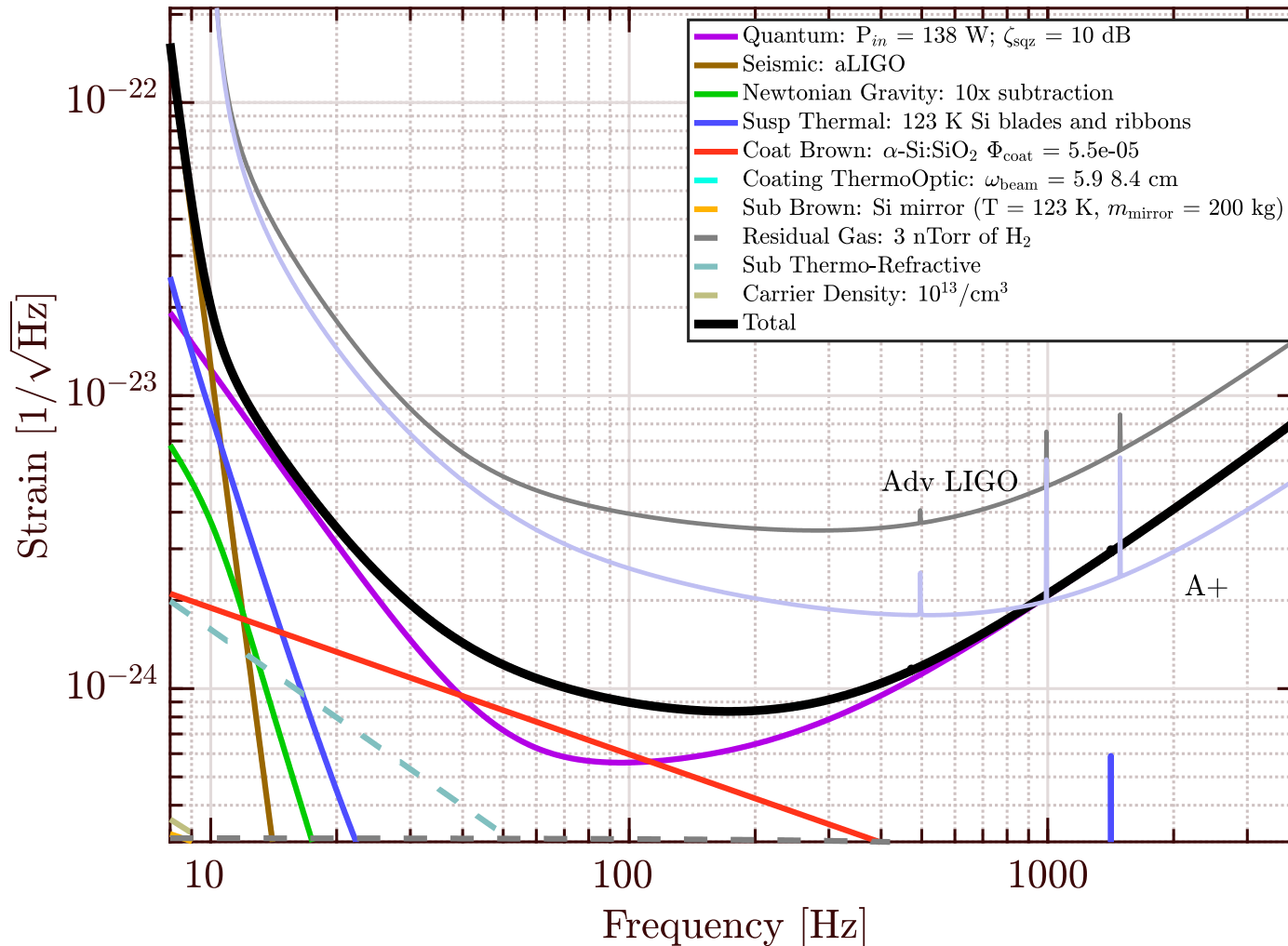
- LIGO Voyager Design and Noise Budget
- Properties of Silicon
- Cryo-Q Experiment
- Non – contact temperature probe
- Modified Setup
- FEA Model
- Circuit Analysis
- Future Work
- Acknowledgement

## Key Updates :

- 200 kg Silicon test masses at 123 K
- 3 MW of arm cavity power
- ~25% increased beam spot size



LIGO Voyager Update presentation by Christopher Wipf (DCC G1900594-v1)



- According to the fluctuation-dissipation theorem, Brownian motion is directly linked to the mechanical damping in the constituent materials of the coating.
- High reflectivity and low mechanical dissipation
- Optical precise measurement → Sense changes in phase of a probe laser beam → Ultra-stable optical interferometers

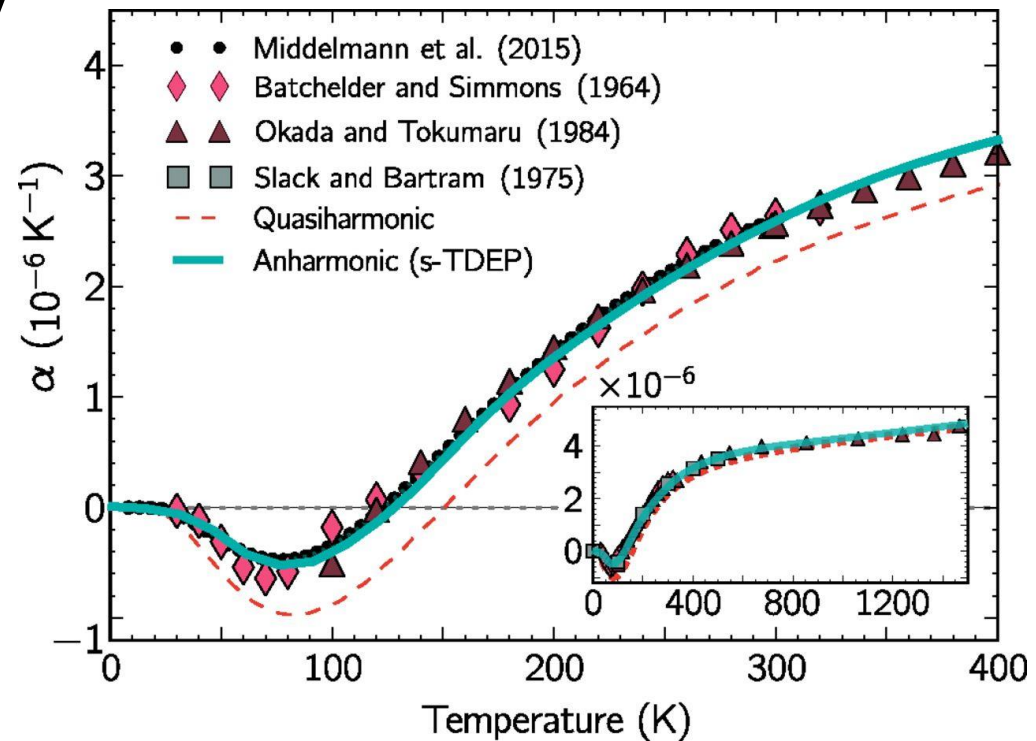
- Coefficient of thermal expansion,  $\alpha \rightarrow 0$  at  $T \sim 123$  K

 Thermo-elastic Noise 

- High thermal Conductivity



Higher Laser Power



Graph reproduced from 'Nuclear quantum effect with pure anharmonicity and the anomalous thermal expansion of silicon', B. Fultz et al.

- According to fluctuation-dissipation relationship,

$$\text{Thermal fluctuations} \propto \frac{1}{Q \text{ factor}}$$

- $Q = 2\pi \left( \frac{\text{Total energy of the system}}{\text{Energy loss per cycle of operation}} \right)$

- $\frac{1}{Q_{Total}} = \sum \frac{1}{Q_{factors}} = \frac{1}{Q_{TED}} + \frac{1}{Q_{Akheizer}} + \frac{1}{Q_{Surface}} + \frac{1}{Q_{Gas}} + \frac{1}{Q_{Others}}$

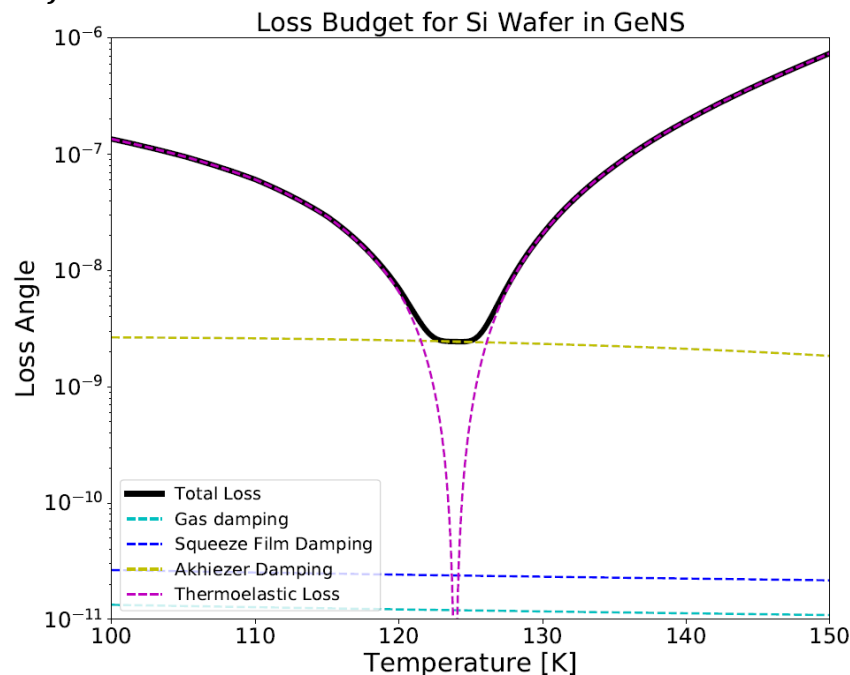
- $Q_{TED} = \left( \frac{\rho C_p}{E \alpha^2 T_0} \right) \frac{1 + (w\tau)^2}{w\tau}$

- Akhiezer damping :

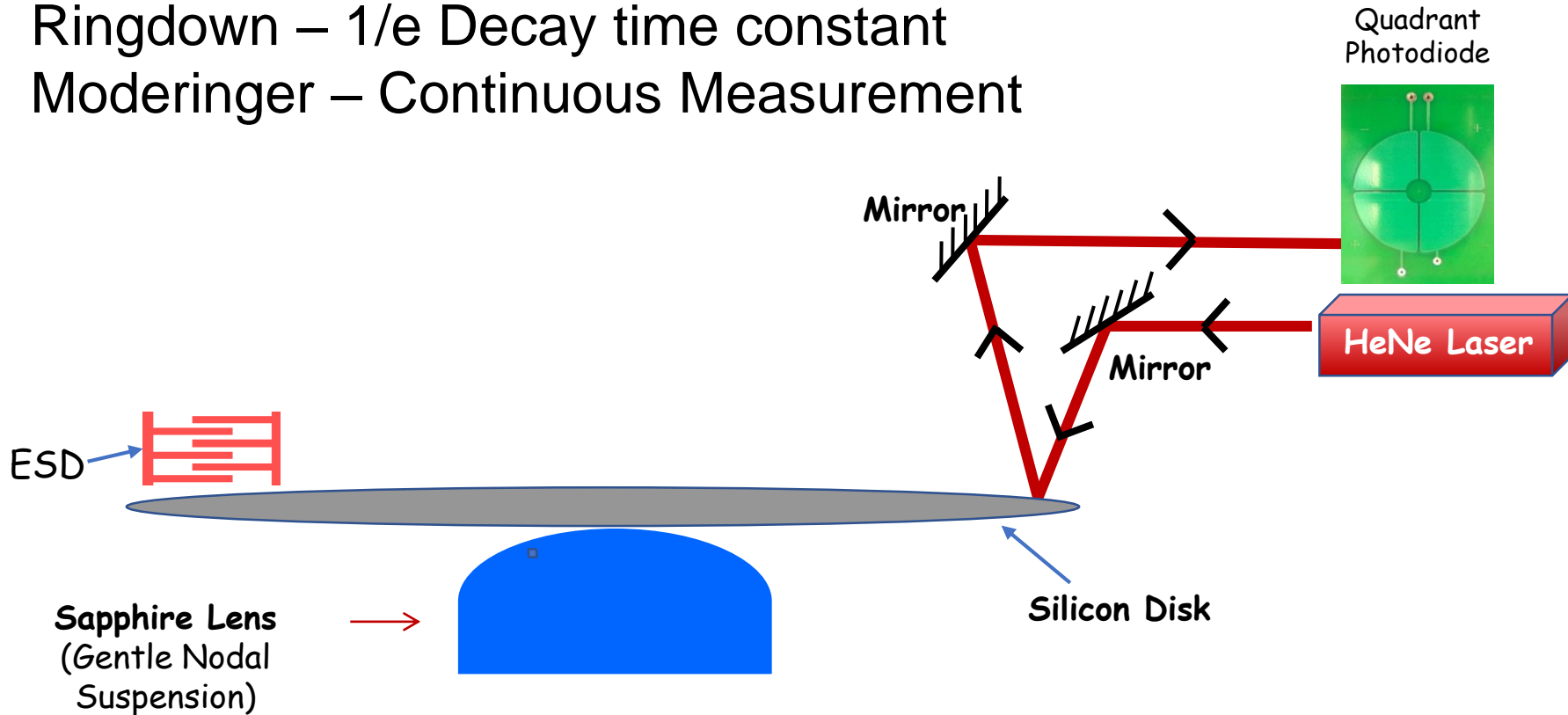
- Phonon-phonon dissipation

- Independent of geometry

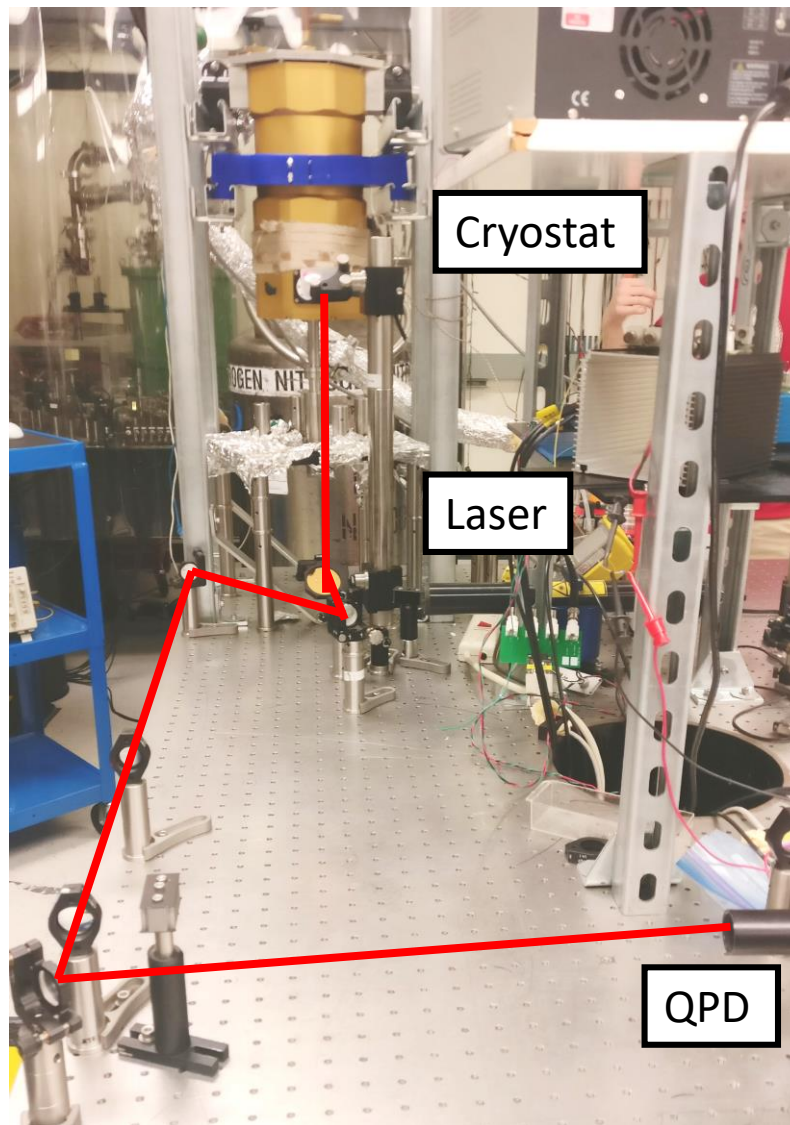
- Determines upper limit of  $Q_{Total}$



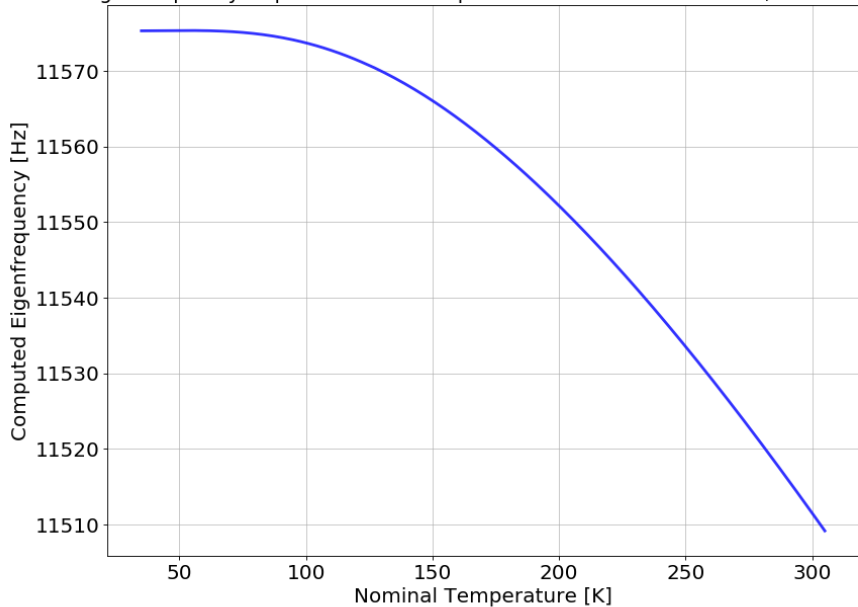
- Gentle Nodal Suspension
- Ringdown –  $1/e$  Decay time constant
- Moderinger – Continuous Measurement



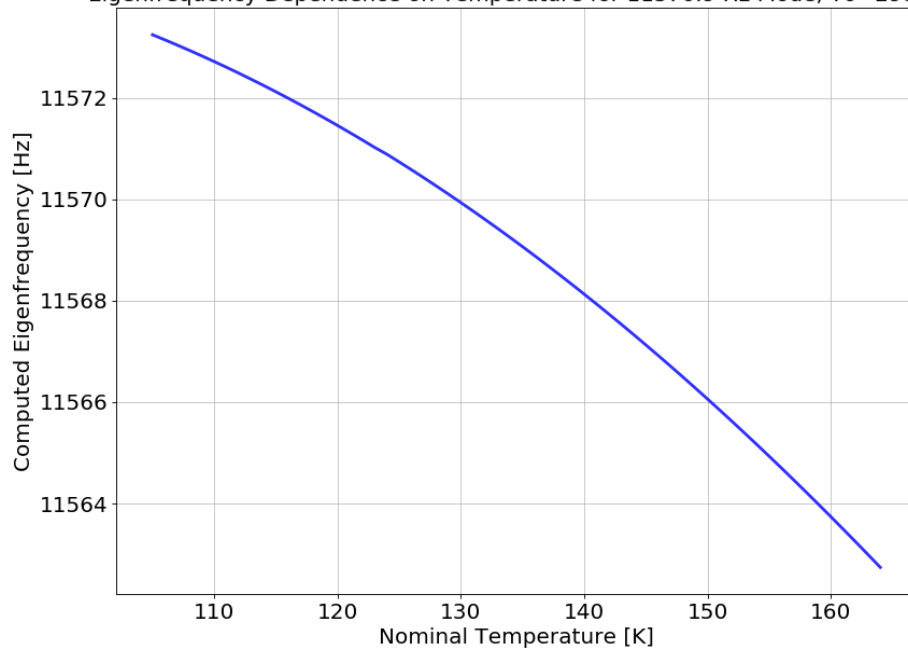


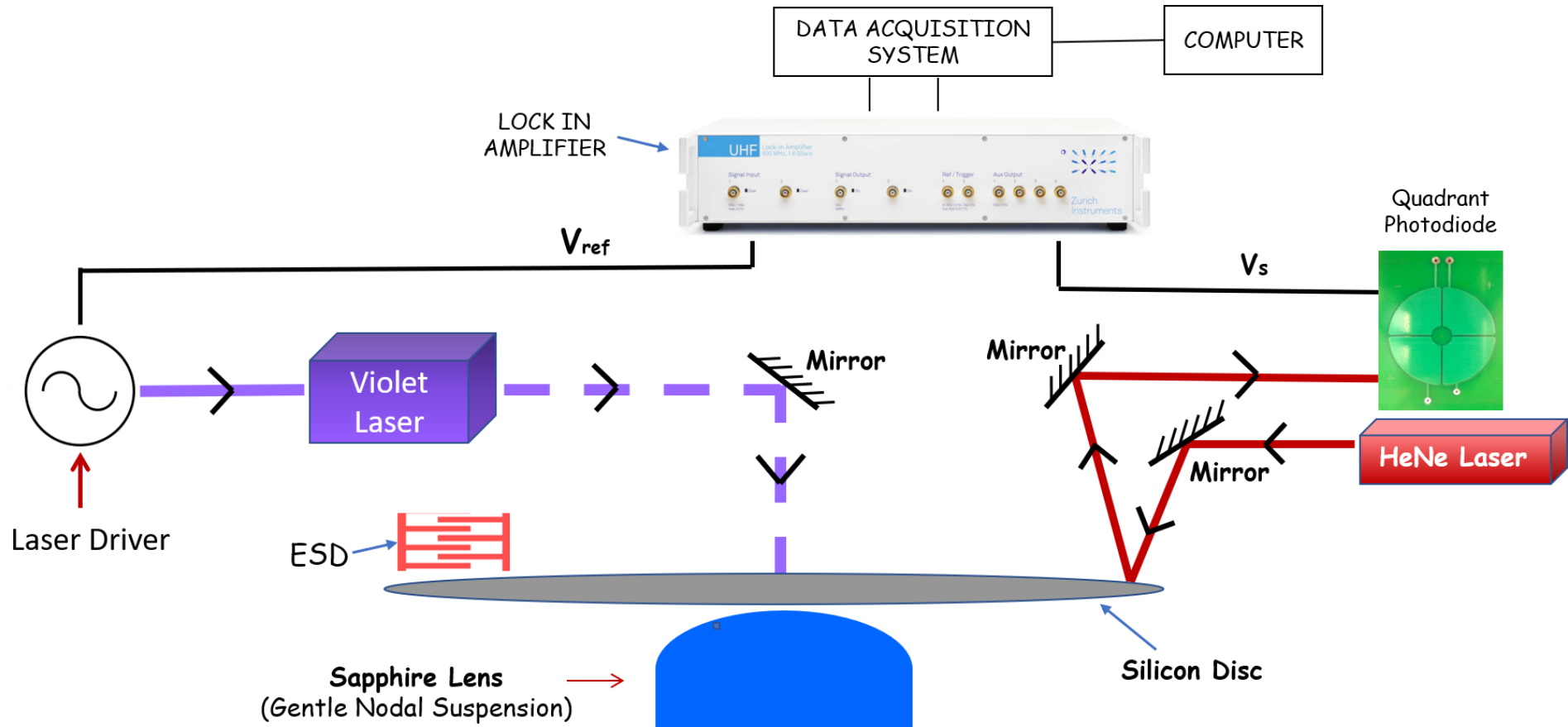


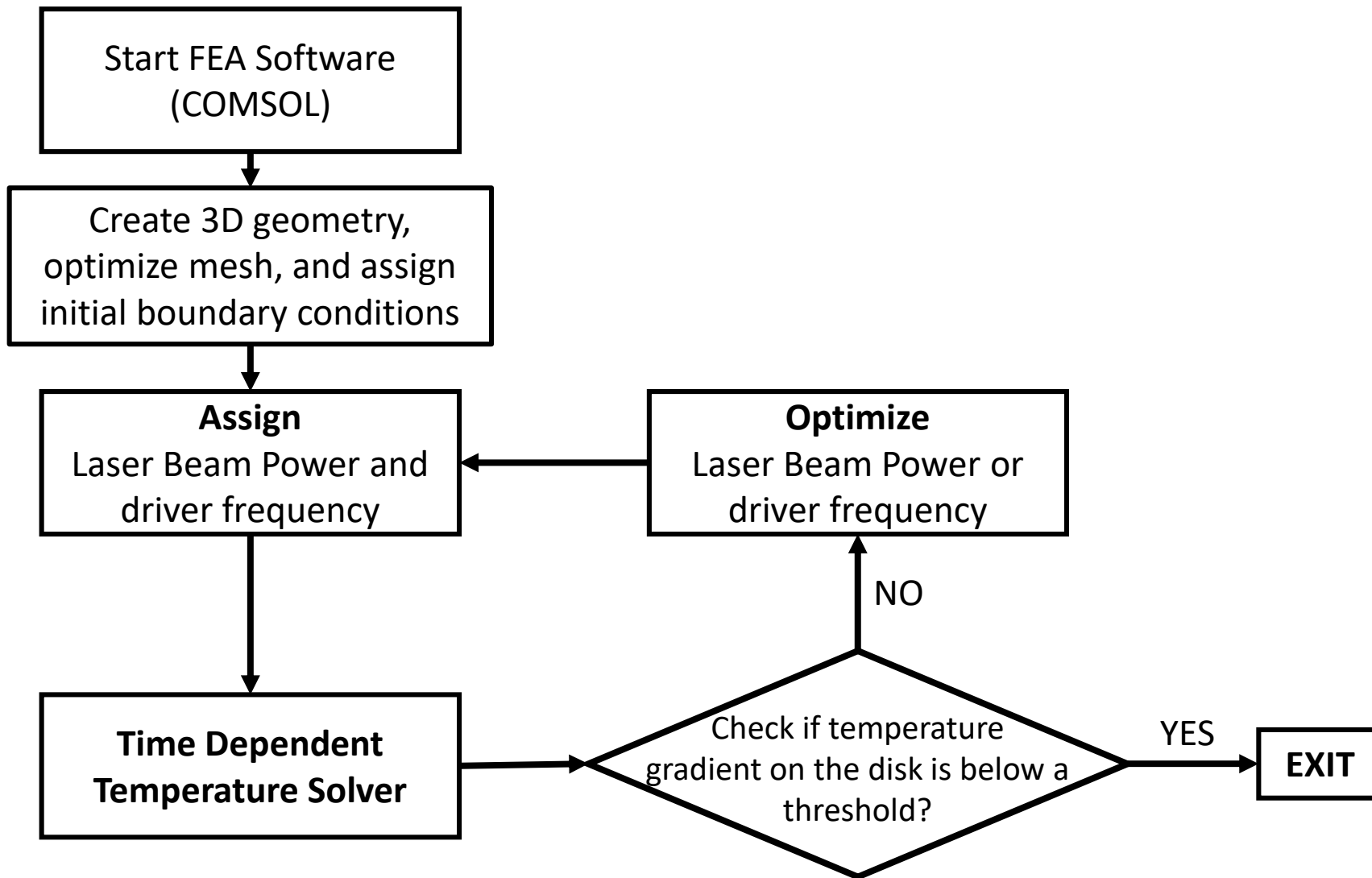
Eigenfrequency Dependence on Temperature for 11570.9 Hz Mode, T<sub>0</sub>=298 K



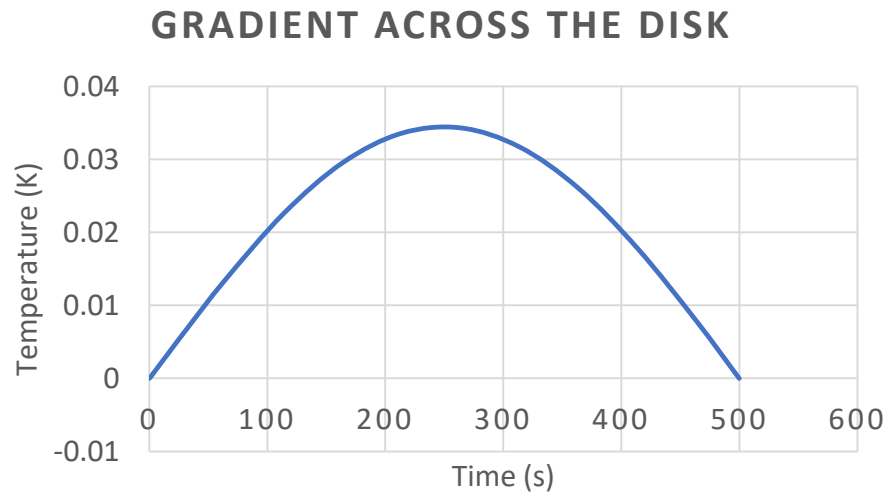
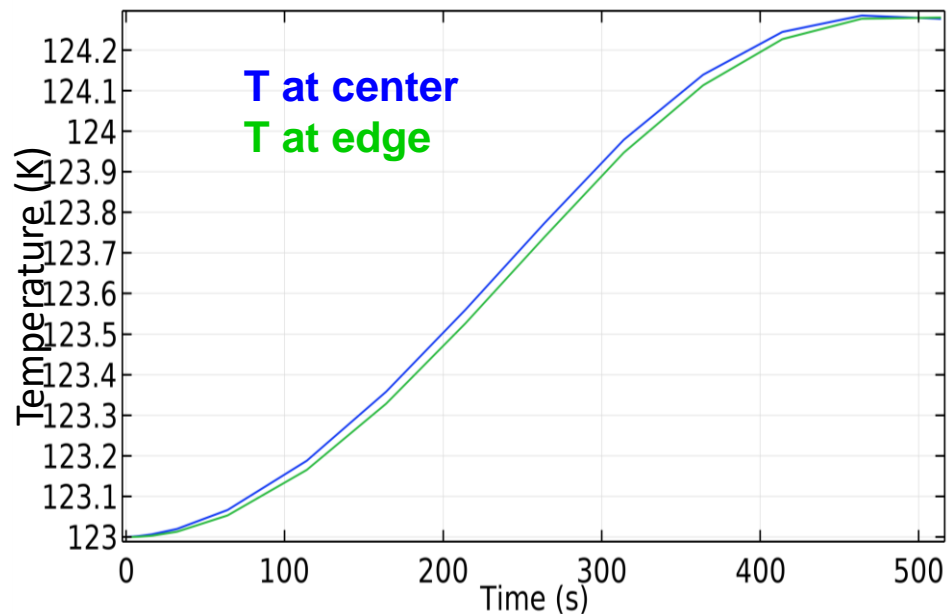
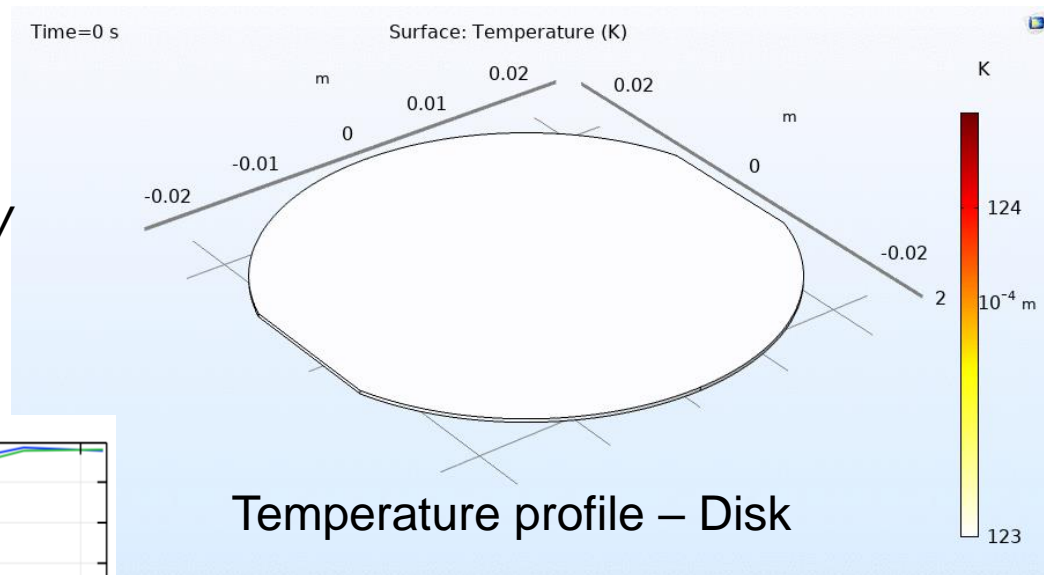
Eigenfrequency Dependence on Temperature for 11570.9 Hz Mode, T<sub>0</sub>=298 K







Gaussian Beam  
 Laser Power :  $5\sin(2\pi \times 0.001 \times t)$  mW  
 Standard Deviation : 2 mm  
 Emissivity of disk :  $3e-4$

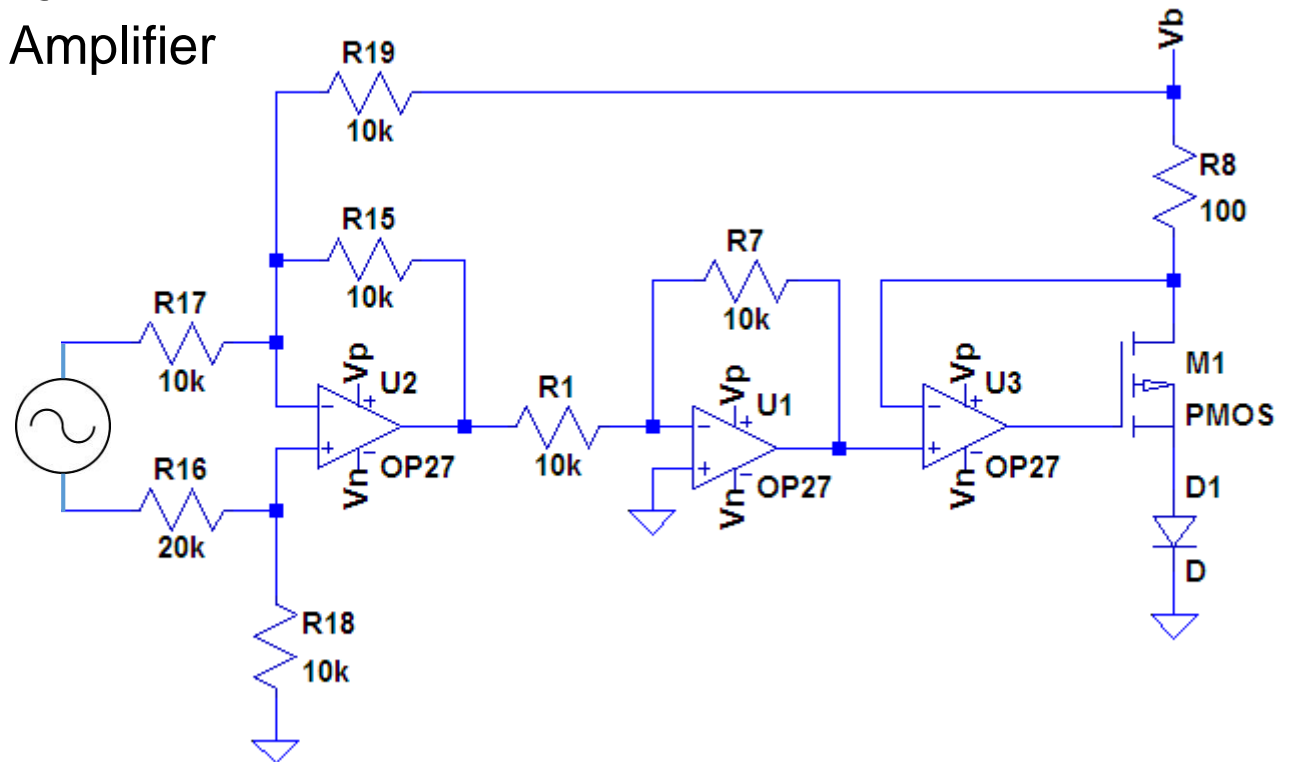


Operating Condition :

U1 : Unity gain Amplifier operating in inverting mode

U2 : Differential Amplifier

U3 : Unity gain Buffer Amplifier





- More data points for the temperature probe
- Faster cooling on the go
  - Increase emissivity of the disk (doped Silicon)
  - To develop a thermally contacted but mechanically isolated system
- Cool down below the zero-crossing temperature (123K)

***THANK YOU***